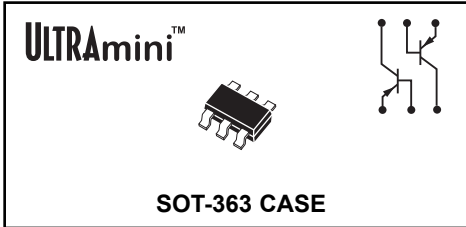


**CMKT2907A**  
**ULTRAmi™**  
**SURFACE MOUNT**  
**DUAL PNP SILICON TRANSISTORS**



# Central™

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMKT2907A consists of two individual isolated 2907A PNP silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-363 surface mount package. This ULTRAmi™ device has been designed for small signal general purpose and switching applications.

**MARKING CODE: K07**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	57	$^\circ\text{C/W}$

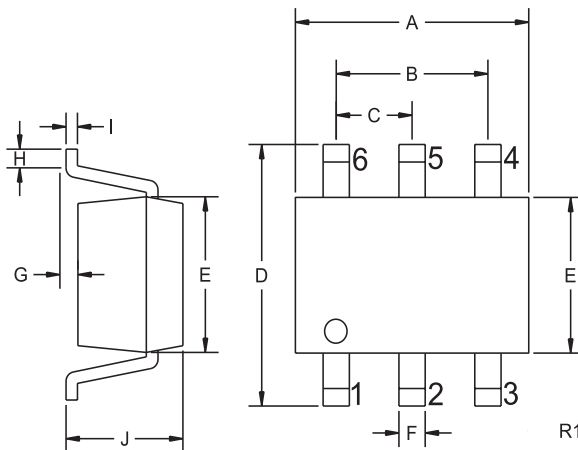
**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{CBO}$	$V_{CB}=50\text{V}$		10	nA
$I_{CBO}$	$V_{CB}=50\text{V}, T_A=125^\circ\text{C}$		10	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$		50	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60		V
$BV_{CEO}$	$I_C=10\text{mA}$	60		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.6	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	75		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	100		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	100		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	50		

**ELECTRICAL CHARACTERISTICS: Continued**

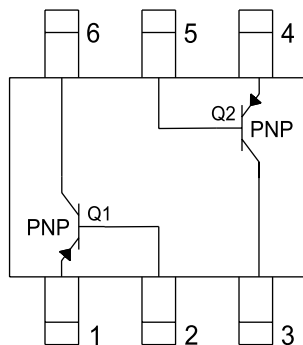
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$f_T$	$V_{CE}=20V, I_C=50mA, f=100MHz$	200		MHz
$C_{ob}$	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
$C_{ib}$	$V_{BE}=2.0V, I_C=0, f=1.0MHz$		30	pF
$t_{on}$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		45	ns
$t_d$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		10	ns
$t_r$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		40	ns
$t_{off}$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		100	ns
$t_s$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		80	ns
$t_f$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		30	ns

**SOT-363 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)



**LEAD CODE:**

- 1) EMITTER Q1
- 2) BASE Q1
- 3) COLLECTOR Q2
- 4) EMITTER Q2
- 5) BASE Q2
- 6) COLLECTOR Q1

**MARKING CODE: K07**